MOSFETs Silicon P-Channel MOS

# SSM6P69NU

#### 1. Applications

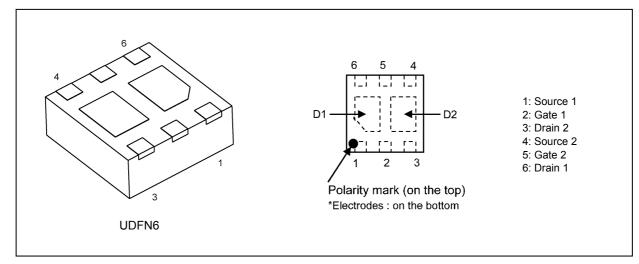
• Power Management Switches

#### 2. Features

- (1) AEC-Q101 qualified (Note 1)
- (2) 1.8 V drive
- (3) Low drain-source on-resistance
  - :  $R_{DS(ON)} = 157 \text{ m}\Omega \text{ (max)} (@V_{GS} = -1.8 \text{ V})$ 
    - $R_{\rm DS(ON)}$  = 76 m $\Omega$  (max) (@V\_{\rm GS} = -2.5 V)
    - $\mathrm{R}_{\mathrm{DS(ON)}}$  = 56 m $\Omega$  (max) (@V\_{\mathrm{GS}} = -4.5 V)
    - $R_{\rm DS(ON)}$  = 45 m $\Omega$  (max) (@V\_{\rm GS} = -10 V)

Note 1: For detail information, please contact to our sales.

### 3. Packaging and Pin Assignment



#### Absolute Maximum Ratings (Note) (Unless otherwise specified, T<sub>a</sub> = 25 °C)(Q1, Q2 Common)

Characteristics					Rating	Unit
Drain-source voltage				V <sub>DSS</sub>	-20	V
Gate-source voltage				V <sub>GSS</sub>	-12/+6	
Drain current (DC)			(Note 1)	I <sub>D</sub>	-4	Α
Drain current (pulsed)			(Note 1), (Note 2)	I <sub>DP</sub>	-16	
Power dissipation			(Note 3)	PD	1	W
Power dissipation	(	t ≤ 10 s)	(Note 3)	PD	2	
Channel temperature				T <sub>ch</sub>	150	°C
Storage temperature				T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150 °C.
- Note 2: Pulse width (PW)  $\leq$  100  $\mu s,\,duty \leq$  1 %

Note 3: Device mounted on an FR4 board. (25.4 mm  $\times$  25.4 mm  $\times$  1.6 mm, Cu pad: 645 mm<sup>2</sup>)

- Note: This transistor is sensitive to electrostatic discharge and should be handled with care.
- Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.
- Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the drain power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

### 5. Electrical Characteristics

### 5.1. Static Characteristics (Unless otherwise specified, Ta = 25 °C)(Q1, Q2 Common)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{DD}$ = 0 V, $V_{GS}$ = -10/+6 V		_	±1	μA
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = -20 V, V <sub>GS</sub> = 0 V			-1	
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	I <sub>D</sub> = -1 mA, V <sub>GS</sub> = 0 V	-20	—	_	V
Drain-source breakdown voltage	(Note 1)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = -1 mA, V <sub>GS</sub> = 8 V	-12	_	_	]
Gate threshold voltage	(Note 2)	V <sub>th</sub>	V <sub>DS</sub> = -3 V, I <sub>D</sub> = -1 mA	-0.5	—	-1.2	
Drain-source on-resistance	(Note 3)	R <sub>DS(ON)</sub>	I <sub>D</sub> = -0.5 A, V <sub>GS</sub> = -1.8 V	—	83	157	mΩ
			I <sub>D</sub> = -2.0 A, V <sub>GS</sub> = -2.5 V		60	76	]
			I <sub>D</sub> = -3.0 A, V <sub>GS</sub> = -4.5 V		44	56	]
			I <sub>D</sub> = -3.5 A, V <sub>GS</sub> = -10 V		36	45	
Forward transfer admittance	(Note 3)	Y <sub>fs</sub>	V <sub>DS</sub> = -3 V, I <sub>D</sub> = -2.0 A	_	9.5	_	s

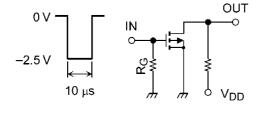
Note 1: If a forward bias is applied between gate and source, this device enters V<sub>(BR)DSX</sub> mode. Note that the drainsource breakdown voltage is lowered in this mode.

Note 3: Pulse measurement.

#### 5.2. Dynamic Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)(Q1, Q2 Common)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	$V_{DS}$ = -10 V , $V_{GS}$ = 0 V,	—	480	—	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz		76	_	
Output capacitance	C <sub>oss</sub>		_	90	_	
Switching time (turn-on time)	t <sub>on</sub>	V <sub>DD</sub> = -10 V, I <sub>D</sub> = -0.5 A, V <sub>GS</sub> = 0 to -2.5 V, R <sub>G</sub> = 4.7 Ω,		21	_	ns
Switching time (turn-off time)		$\begin{array}{l} Duty \leq 1\%, \ V_{IN}: t_r, t_f < 5 \ ns, \\ Common \ source, \ See \ chapter \ 5.3. \end{array}$		54	_	

#### 5.3. Switching Time Test Circuit



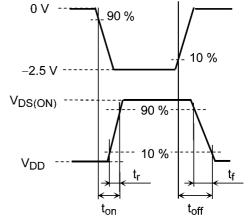


Fig. 5.3.1 Switching Time Test Circuit

Fig. 5.3.2 Input Waveform/Output Waveform

Note 2: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current (I<sub>D</sub>) to below (-1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ . Take this into consideration when using the device.

#### 5.4. Gate Charge Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)(Q1, Q2 Common)

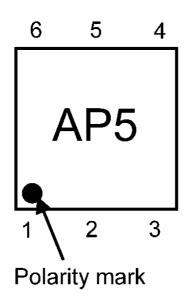
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	V <sub>DD</sub> = -10 V, I <sub>D</sub> = -4.0 A,	_	6.74		nC
Gate-source charge 1	Q <sub>gs1</sub>	V <sub>GS</sub> = -4.5 V	_	0.95	_	
Gate-drain charge	Q <sub>gd</sub>		_	1.50	_	

#### 5.5. Source-Drain Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)(Q1, Q2 Common)

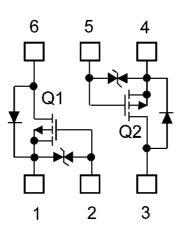
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	(Note 1)	$V_{DSF}$	I <sub>D</sub> = 4.0 A, V <sub>GS</sub> = 0 V		0.87	1.2	V

Note 1: Pulse measurement.

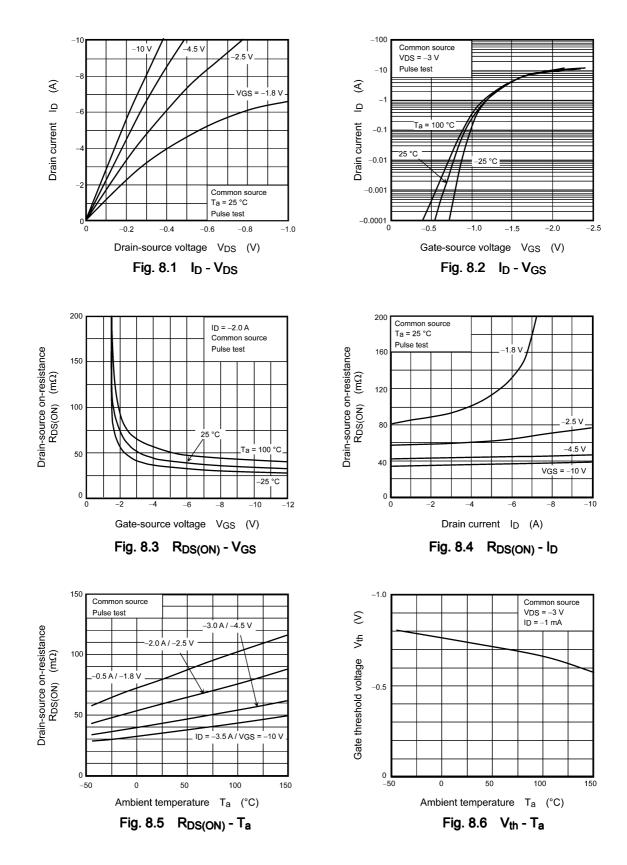
#### 6. Marking



7. Internal Equivalent Circuit



### 8. Characteristics Curves (Q1, Q2 Common) (Note)



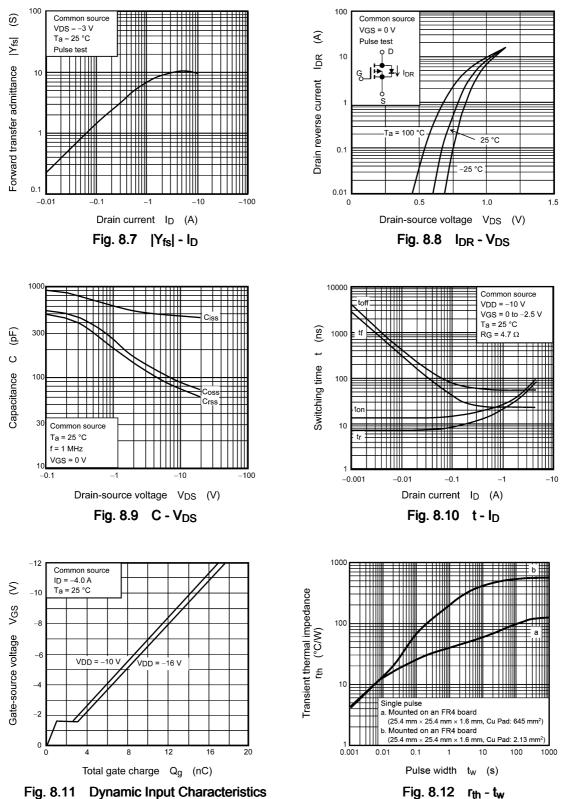
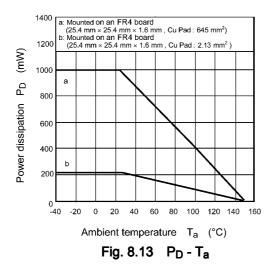


Fig. 8.11 Dynamic Input Characteristics



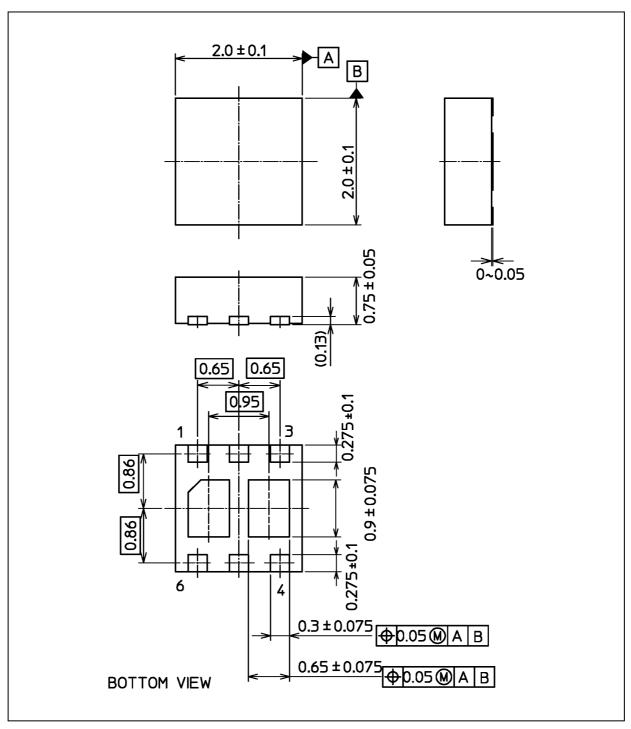
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



### SSM6P69NU

#### **Package Dimensions**

Unit: mm



#### Weight: 8.5 mg (typ.)

	Package Name(s)
JEDEC: SOT-1118	
Nickname: UDFN6	

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